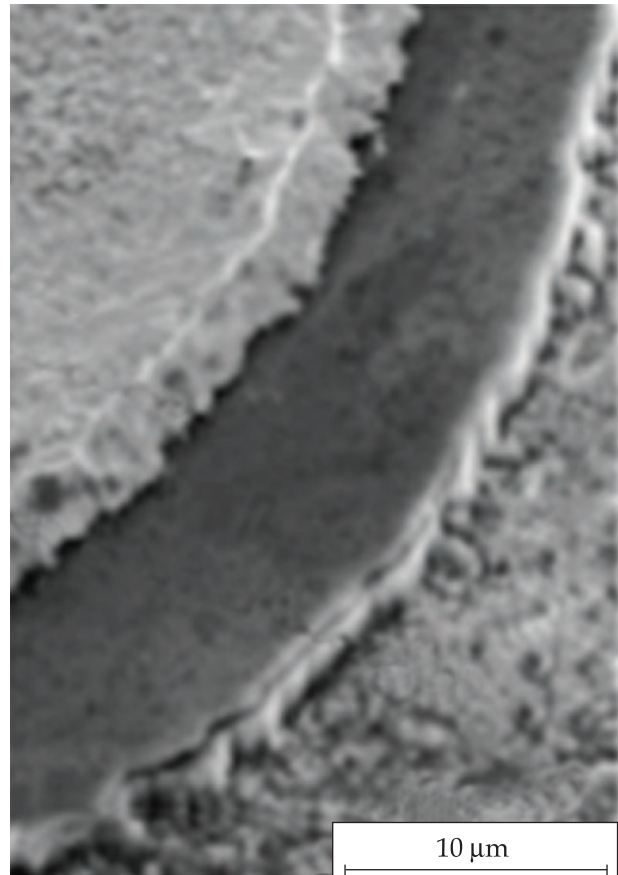
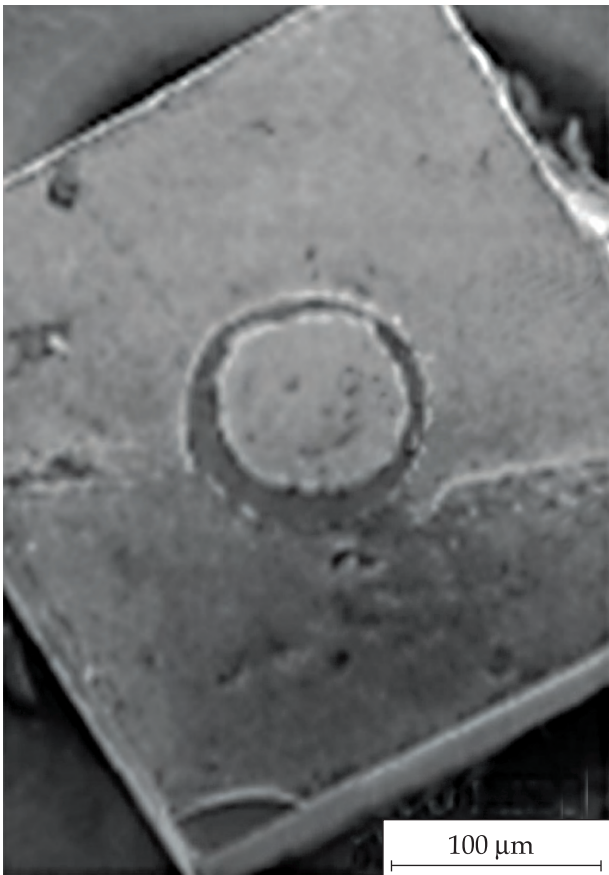


HIGH-SPEED DIODE



Areas of Application

To switch signals in microwave devices

Specification

The *p-i-n* type diode is based on carbide-silicon mesostructured; switches microwave signals with a power up to 2 kW. The diodes can operate at a temperature up to 500 °C. The diode reverse voltage is 630 V, at a room temperature, and 250 V, at 500 °C

Stage of Development.

Suggestions for Commercialization

IRL6, TRL6

Manufacture and supply in cooperation with *Orion* R&D Institute

Advantages

The diode surpasses the foreign counterparts in capacity and operating temperature

IPR Protection

IPR1

Contact Information

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